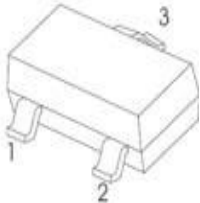
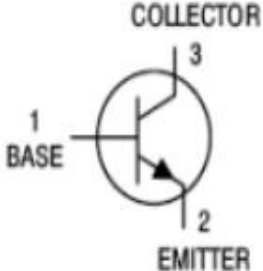


TRANSISTOR (PNP)	SOT-23 Plastic-Encapsulate Transistors		
<p><u>SOT-23</u></p>   <p>1.BASE 2.EMITTER 3.COLLECTOR</p> <p>Marking :2A</p>	<p><b>Features</b></p> <ul style="list-style-type: none"> <li>※ Complimentary to MMBT3904</li> <li>※ Collector Current: <math>I_c=200\text{mA}</math></li> </ul>		
<b>MAXIMUM RATINGS (Ta=25°C unless otherwise noted)</b>			
<b>Parameter</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Collector-Base Voltage	VCBO	-40	V
Collector-Emitter Voltage	VCEO	-40	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current	IC	-200	mA
Collector Power Dissipation	PC	200	mW
Thermal Resistance From Junction To Ambient	RθJA	325	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= -10μA, IE=0	-40			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -1mA, IB=0	-40			V
Emitter-base breakdown voltage	V(BR)EBO	IE= -10μA, IC=0	-5			V
Collector cut-off current	ICBO	VCB= -40 V , IE=0			-0.1	μA
Collector cut-off current	ICEO	VCE=-30V, VBE(off)=-3V			-50	nA
Emitter cut-off current	IEBO	VEB= -6V , IC=0			-0.1	μA
DC current gain	hFE	VCE= -1V, IC= -10mA	100		300	
	hFE	VCE= -1V, IC= -50mA	60			
	hFE	VCE= -1V, IC= -100mA	30			
Collector-emitter saturation voltage	VCE(sat)	IC= -50 mA, IB= -5mA			-0.3	V
Base-emitter saturation voltage	VBE(sat)	IC= -50 mA, IB= -5mA			-1	V
Transition frequency	fT	VCE=6V, IC= 20mA f=30MHz	300			MHz
Delay time	td	VCC=3V, VBE=0.5V, IC=10mA, IB=1mA,			35	ns
Rise time	tr	VCC=3V, VBE=0.5V, IC=10mA, IB=1mA,			35	ns
Storage time	ts	VCC=3V, VBE=0.5V, IC=10mA, IB=1mA,			225	ns
Fall time	tf	VCC=3V, VBE=0.5V, IC=10mA, IB=1mA,			75	ns
<b>CLASSIFICATION OF hFE</b>						
<b>HFE</b>	<b>100-300</b>					

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

